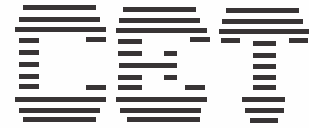


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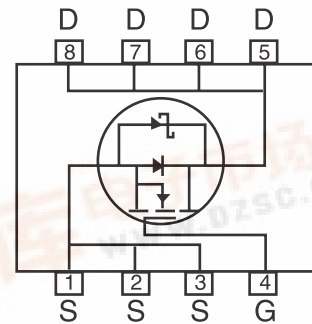
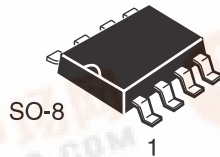


PRELIMINARY

## N-Channel Enhancement Mode Field Effect Transistor

### FEATURES

- 30V , 7A ,  $R_{DS(ON)}=28m\Omega$  @ $V_{GS}=10V$ .  
 $R_{DS(ON)}=42m\Omega$  @ $V_{GS}=4.5V$ .
- Super high dense cell design for extremely low  $R_{DS(ON)}$ .
- High power and current handling capability.
- Surface mount package.



### ABSOLUTE MAXIMUM RATINGS ( $T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	30	V
Gate-Source Voltage	VGS	$\pm 20$	V
Drain Current-Continuous @ $T_J=125^{\circ}C$ -Pulsed	ID	$\pm 7$	A
	IDM	$\pm 30$	A
Drain-Source Diode Forward Current	IS	2.3	A
Maximum Power Dissipation	PD	2.5	W
Operating Junction and Storage Temperature Range	TJ, TSTG	-55 to 150	$^{\circ}C$

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### THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	50	$^{\circ}C/W$
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## ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			10	μA
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V			±100	nA
<b>ON CHARACTERISTICS<sup>b</sup></b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1	1.5	3	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =7A		20	28	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =3.5A		28	42	mΩ
On-State Drain Current	I <sub>D(ON)</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =5V	30			A
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =15V, I <sub>D</sub> =7A		16		S
<b>DYNAMIC CHARACTERISTICS<sup>c</sup></b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V f=1.0MHz		707	920	pF
Output Capacitance	C <sub>OSS</sub>			355	460	pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			89	120	pF
<b>SWITCHING CHARACTERISTICS<sup>c</sup></b>						
Turn-On Delay Time	t <sub>D(ON)</sub>	V <sub>DD</sub> =25V, I <sub>D</sub> =1A, V <sub>GEN</sub> =10V, R <sub>GEN</sub> =6Ω		8	15	ns
Rise Time	t <sub>r</sub>			11	20	ns
Turn-Off Delay Time	t <sub>D(OFF)</sub>			35	55	ns
Fall Time	t <sub>f</sub>			17	28	ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =15V, I <sub>D</sub> =2A, V <sub>GS</sub> =10V		23	29	nC
Gate-Source Charge	Q <sub>gs</sub>			3		nC
Gate-Drain Charge	Q <sub>gd</sub>			4		nC

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## BODY DIODE & SCHOTTKY DIODE RATINGS AND CHARACTERISTICS

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>DRAIN-SOURCE DIODE CHARACTERISTICS<sup>b</sup></b>						
Body Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_S = 2.0A$		0.76	1.1	V
Schottky Forward Voltage	$V_F$	$I_F = 2A, T_C = 25^\circ C$			0.55	V
Average Forward Rectified Current	$I_{F(AV)}$				1	A

### Notes

- a. Pulse Test: Pulse Width  $\leq 300 \mu s$ , Duty Cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.

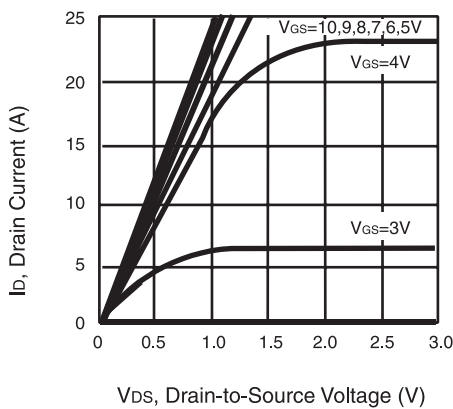


Figure 1. Output Characteristics

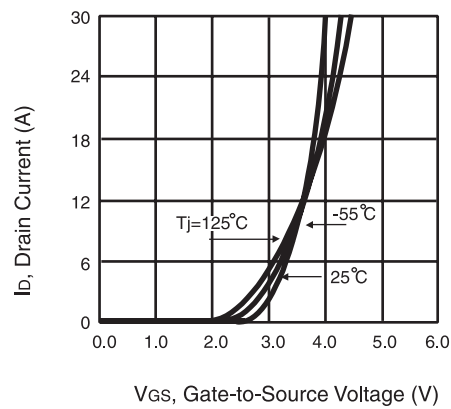


Figure 2. Transfer Characteristics

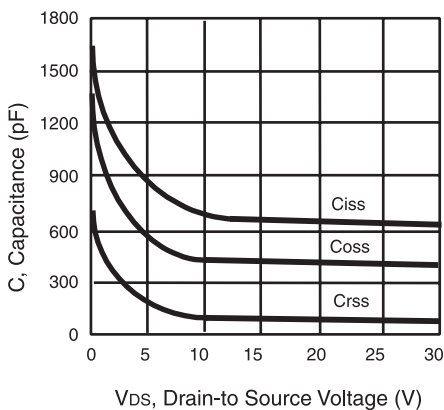


Figure 3. Capacitance

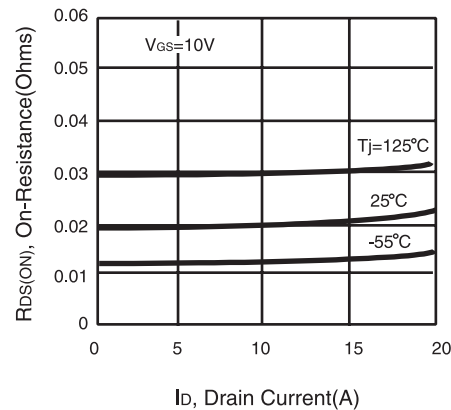
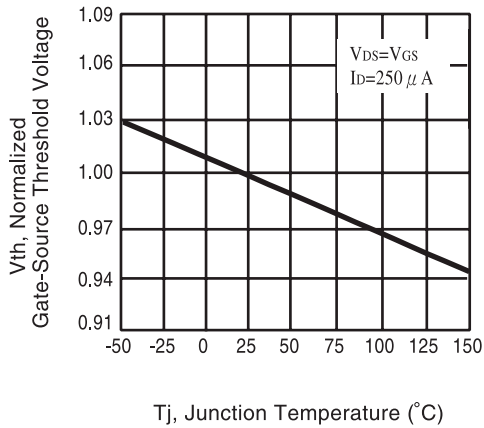
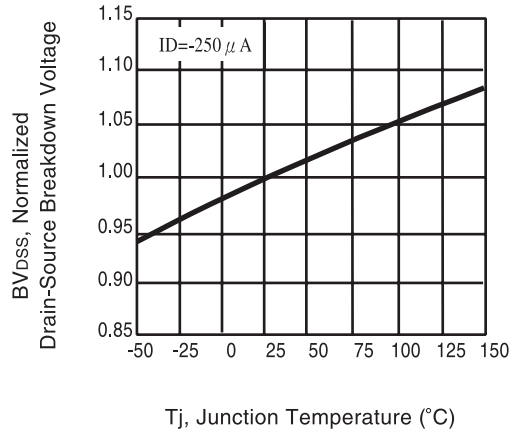


Figure 4. On-Resistance Variation with Drain Current and Temperature

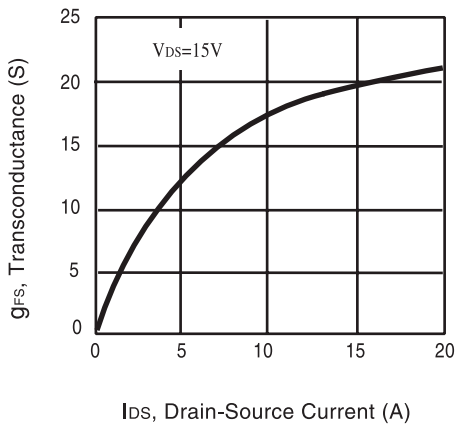
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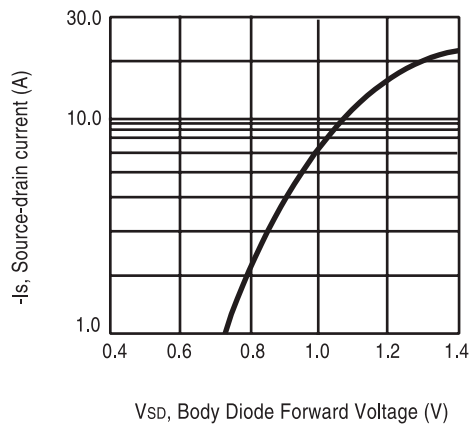
**Figure 5. Gate Threshold Variation with Temperature**



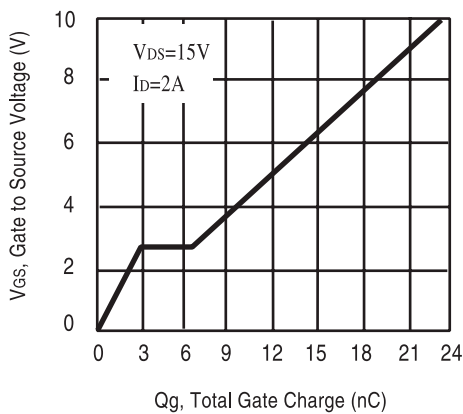
**Figure 6. Breakdown Voltage Variation with Temperature**



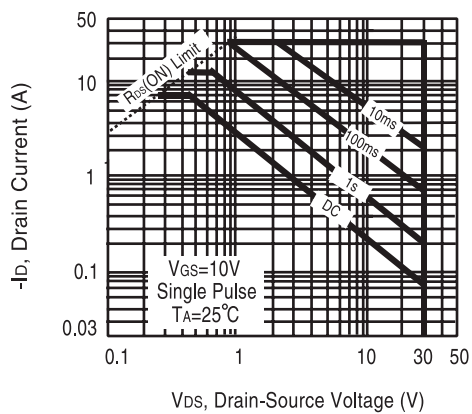
**Figure 7. Transconductance Variation with Drain Current**



**Figure 8. Body Diode Forward Voltage Variation with Source Current**



**Figure 9. Gate Charge**



**Figure 10. Maximum Safe Operating Area**

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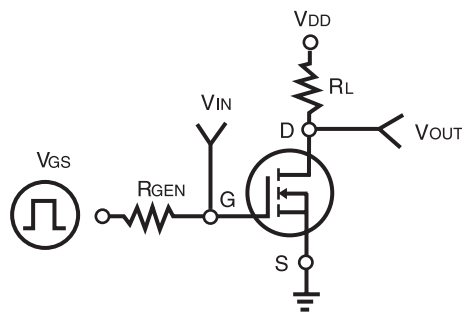


Figure 11. Switching Test Circuit

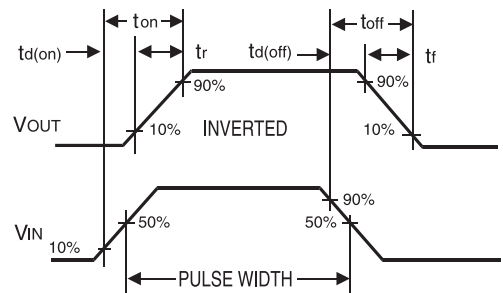


Figure 12. Switching Waveforms

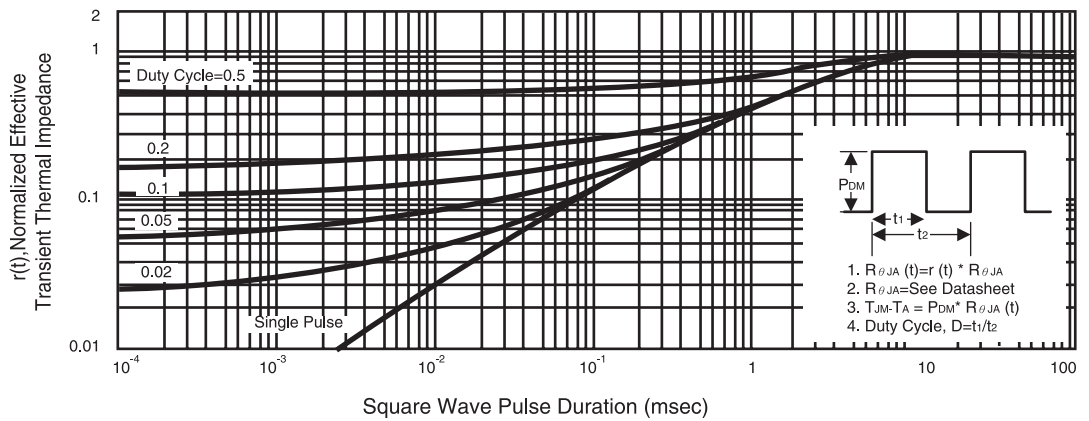


Figure 13. Normalized Thermal Transient Impedance Curve